CY62138EV30
MoBL®

2-Mbit (256K x 8) MoBL® Static RAM

Features

- **Very high speed: 45 ns**
  - **Wide voltage range: 2.20V – 3.60V**
- **Pin-compatible with CY62138CV30**
- **Ultra-low standby power**
  - **Typical standby current: 1 μA**
  - **Maximum standby current: 7 μA**
- **Ultra-low active power**
  - **Typical active current: 2 mA @ f = 1 MHz**
- **Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Offered in Pb-free 36-ball BGA package**

Functional Description[1]

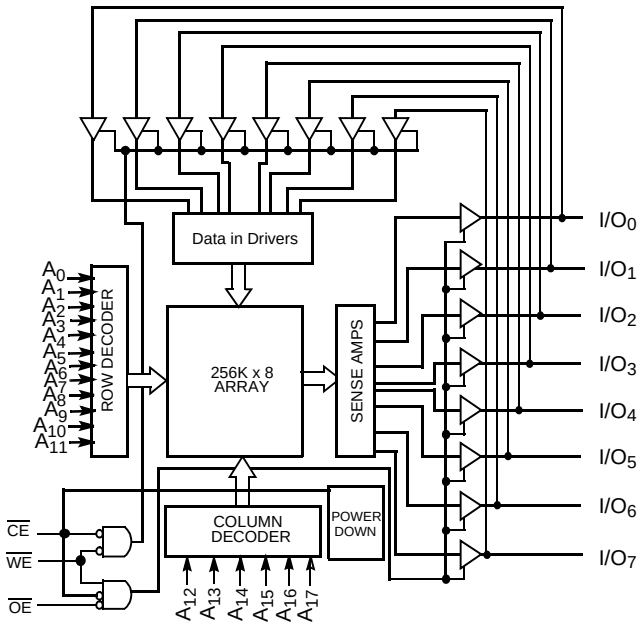
The CY62138EV30 is a high-performance CMOS static RAM organized as 256K words by 8 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly reduces power consumption. The device can be put into standby mode reducing power consumption when deselected ($\overline{CE}$ HIGH).

Writing to the device is accomplished by taking Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. Data on the eight I/O pins (I/O_0 through I/O_7) is then written into the location specified on the address pins (A_0 through A_{18}).

Reading from the device is accomplished by taking Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing Write Enable ($\overline{WE}$) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input/output pins (I/O_0 through I/O_7) are placed in a high-impedance state when the device is deselected ($\overline{CE}$ HIGH), the outputs are disabled ($\overline{OE}$ HIGH), or during a write operation ($\overline{CE}$ LOW and $\overline{WE}$ LOW).

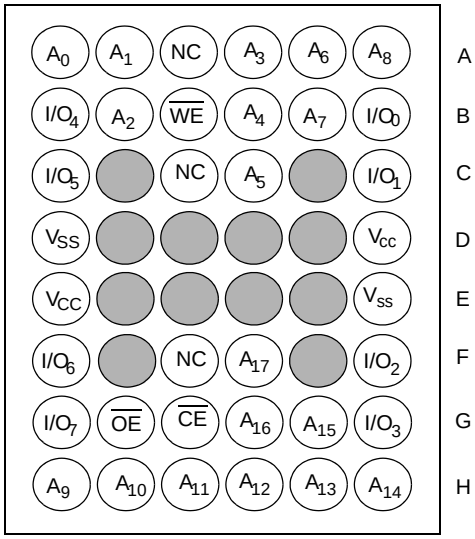
Logic Block Diagram



Note:
1. For best practice recommendations, please refer to the Cypress application note “System Design Guidelines” on http://www.cypress.com.

Pin Configuration[2]

FBGA
Top View



Product Portfolio

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I_{CC} (mA)				Standby I_{SB2} (µA)	
					f = 1 MHz		f = f_{max}			
	Min.	Typ.[3]	Max.		Typ.[3]	Max.	Typ.[3]	Max.	Typ.[3]	Max.
CY62138EV30LL	2.2	3.0	3.6	45	2	2.5	15	20	1	7

Notes:
2. NC pins are not connected on the die.
3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ.)}$, $T_A = 25°C$.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... –65°C to +150°C

Ambient Temperature with Power Applied..... 55°C to +125°C

Supply Voltage to Ground Potential ..... –0.3V to $V_{CC(MAX)}$ + 0.3V

DC Voltage Applied to Outputs in High-Z State[4,5]..... –0.3V to $V_{CC(MAX)}$ + 0.3V

DC Input Voltage[4,5]..... –0.3V to $V_{CC(MAX)}$ + 0.3V

Output Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current..... > 200 mA

Product	Range	Ambient Temperature	V_{CC}[6]
CY62138EV30LL	Industrial	–40°C to +85°C	2.2V to 3.6V

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		CY62138EV30-45 Min.	Typ.[3]	Max.	Unit
V_{OH}	Output HIGH Voltage	I_{OH} = –0.1 mA	V_{CC} = 2.20V	2.0			V
		I_{OH} = –1.0 mA	V_{CC} = 2.70V	2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA	V_{CC} = 2.20V			0.4	V
		I_{OL} = 2.1 mA	V_{CC} = 2.70V			0.4	V
V_{IH}	Input HIGH Voltage	V_{CC} = 2.2V to 2.7V		1.8		V_{CC} + 0.3V	V
		V_{CC}= 2.7V to 3.6V		2.2		V_{CC} + 0.3V	V
V_{IL}	Input LOW Voltage	V_{CC} = 2.2V to 2.7V		–0.3		0.6	V
		V_{CC}= 2.7V to 3.6V		–0.3		0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = $1/t_{RC}$	V_{CC} = V_{CCmax}, I_{OUT} = 0 mA, CMOS levels		15	20	mA
		f = 1 MHz			2	2.5	mA
I_{SB1}	Automatic CE Power-down Current — CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V, V_{IN} ≤ 0.2V), f = f_{MAX} (Address and Data Only), f = 0 (OE, and WE), V_{CC} = 3.60V			1	7	µA
I_{SB2}	Automatic CE Power-down Current — CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = 3.60V			1	7	µA

Capacitance for all packages[7]

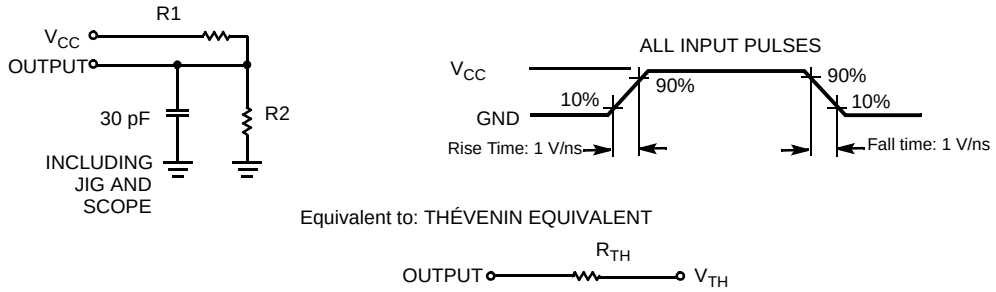
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ.)}$	10	pF
C_{OUT}	Output Capacitance		10	pF

Notes:
4. $V_{IL(min.)}$ = –2.0V for pulse durations less than 20 ns.
5. $V_{IH(max)}$ = V_{CC}+0.75V for pulse durations less than 20 ns.
6. Full device AC operation assumes a 100 µs ramp time from 0 to V_{CC}(min.) and 200 µs wait time after V_{CC} stabilization.

Thermal Resistance

Parameter	Description	Test Conditions	BGA	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 x 4.5 inch, four-layer printed circuit board	72	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		8.86	°C/W

AC Test Loads and Waveforms

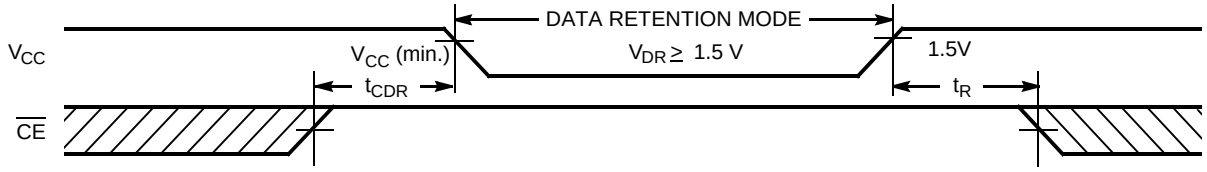


Parameters	2.50V	3.0V	Unit
R1	16667	1103	Ω
R2	15385	1554	Ω
R_{TH}	8000	645	Ω
V_{TH}	1.20	1.75	V

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min.	Typ.[3]	Max.	Unit
V_{DR}	V_{CC} for Data Retention		1			V
I_{CCDR}	Data Retention Current	V_{CC} = 1V, $\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$		0.8	3	µA
t_{CDR}[7]	Chip Deselect to Data Retention Time		0			ns
t_R[8]	Operation Recovery Time		t_{RC}			ns

Data Retention Waveform



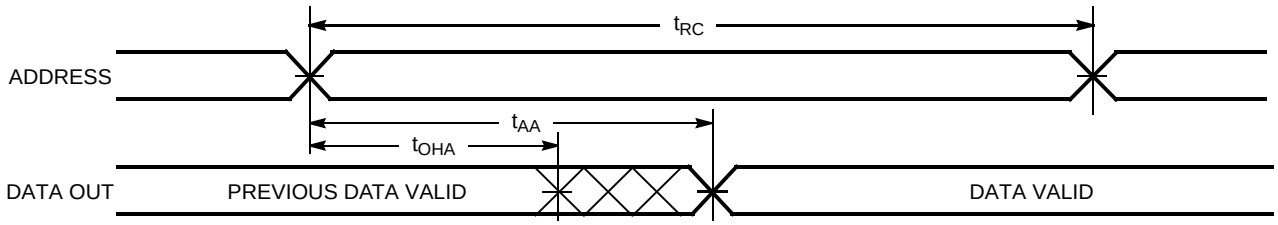
Notes:
7. Tested initially and after any design or process changes that may affect these parameters.
8. Full Device AC operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)} \geq 100$ µs or stable at $V_{CC(min.)} \geq 100$ µs.

Switching Characteristics (Over the Operating Range)[9]

Parameter	Description	45 ns		Unit
		Min.	Max.	
Read Cycle				
t_{RC}	Read Cycle Time	45		ns
t_{AA}	Address to Data Valid		45	ns
t_{OHA}	Data Hold from Address Change	10		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		45	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		22	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[10]	5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[10,11]		18	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[10]	10		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[10, 11]		18	ns
t_{PU}	$\overline{CE}$ LOW to Power-up	0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-up		45	ns
Write Cycle[12]				
t_{WC}	Write Cycle Time	45		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	35		ns
t_{AW}	Address Set-up to Write End	35		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Set-up to Write Start	0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	35		ns
t_{SD}	Data Set-up to Write End	25		ns
t_{HD}	Data Hold from Write End	0		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[10, 11]		18	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[10]	10		ns

Switching Waveforms

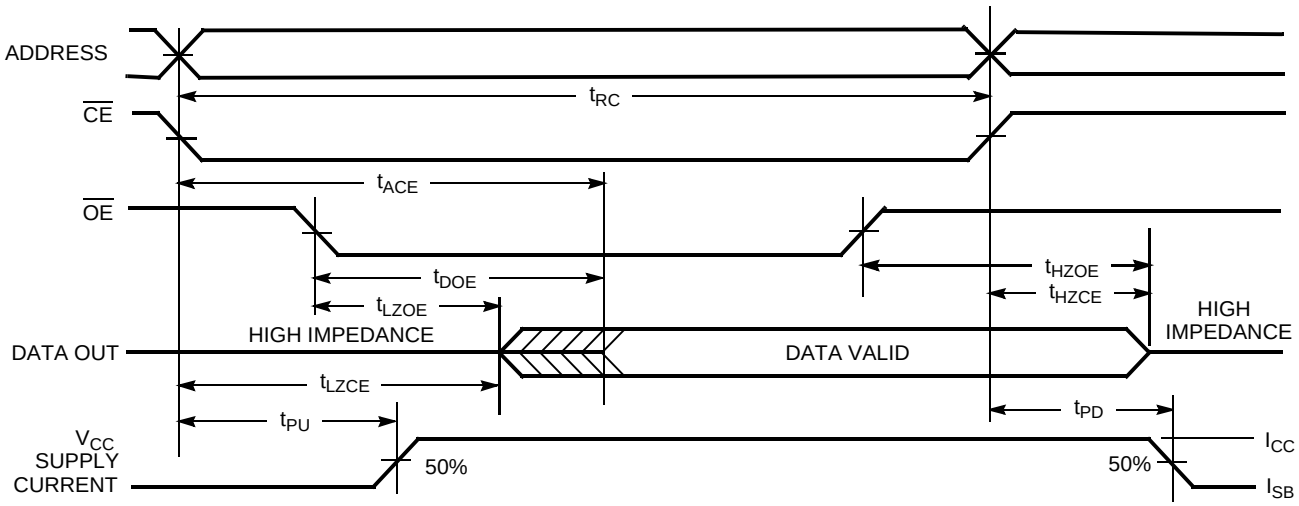
Read Cycle No. 1 (Address Transition Controlled)[13, 14]



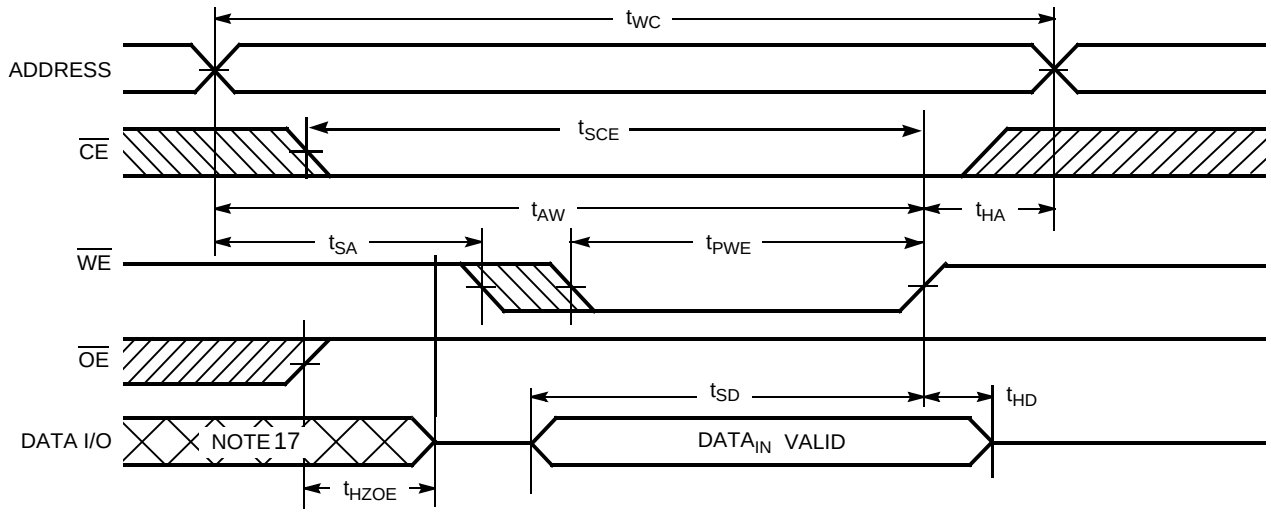
Notes:
9. Test Conditions for all parameters other than three-state parameters assume signal transition time of 3 ns or less (1 V/ns), timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0 to $V_{CC(typ)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the “AC Test Loads and Waveforms” section.
10. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
11. t_{HZOE}, t_{HZCE}, and t_{HZWE} transitions are measured when the output enter a high-impedance state.
12. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.
13. Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}.
14. $\overline{WE}$ is HIGH for read cycle.

Switching Waveforms (continued)

Read Cycle No. 2 (OE Controlled)[14, 15]



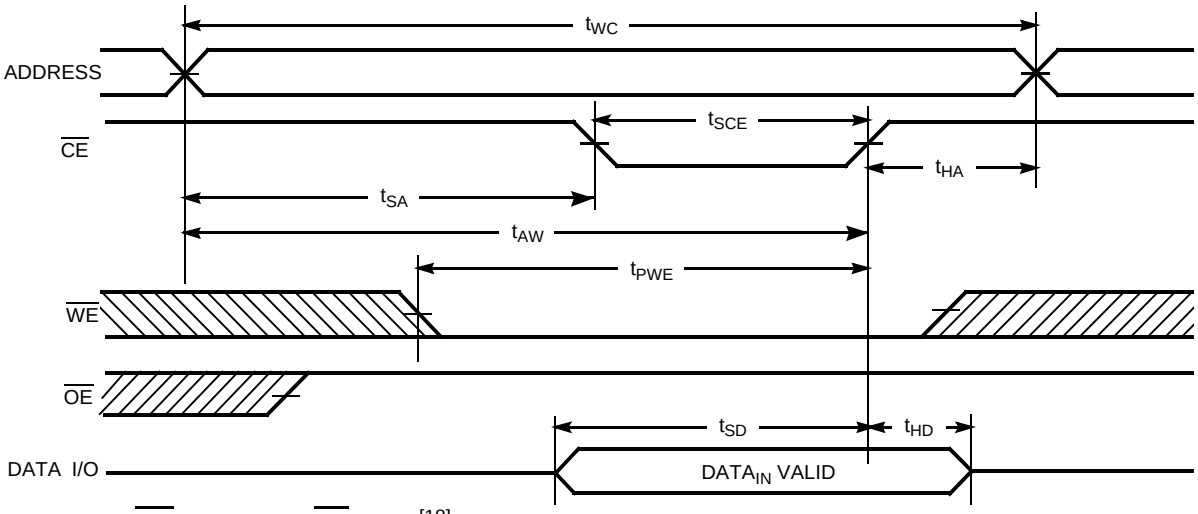
Write Cycle No. 1 (WE Controlled)[16, 18]



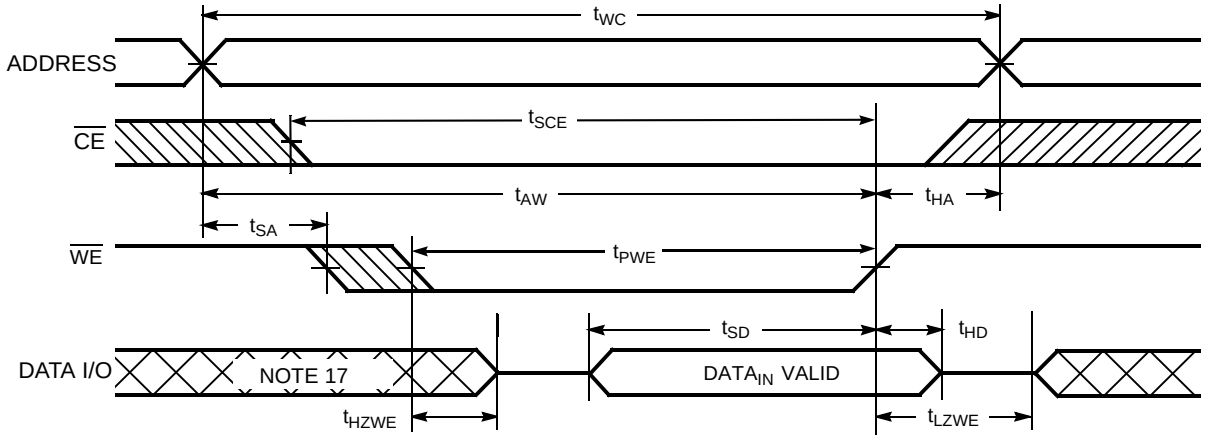
Notes:
15. Address valid prior to or coincident with CE transition LOW.
16. Data I/O is high impedance if OE = V_{IH}.
17. During this period, the I/Os are in output state and input signals should not be applied.
18. If CE goes HIGH simultaneously with WE HIGH, the output remains in high-impedance state.

Switching Waveforms (continued)

Write Cycle No. 2 ($\overline{CE}$ Controlled)[16, 18]



Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)[18]



Truth Table

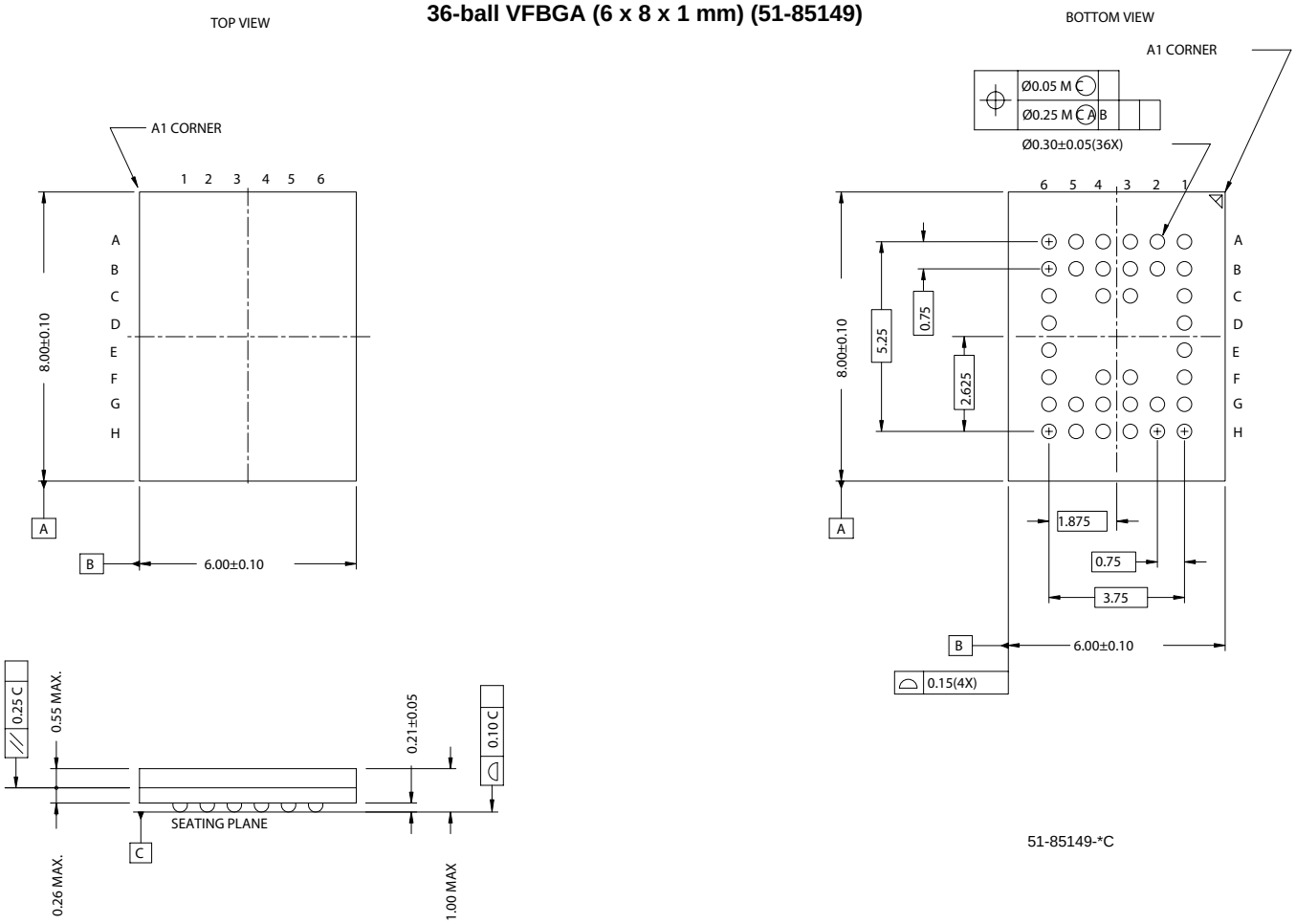
$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	Inputs/Outputs	Mode	Power
H	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
L	H	L	Data Out (I/O_0–I/O_7)	Read	Active (I_{CC})
L	H	H	High Z	Output Disabled	Active (I_{CC})
L	L	X	Data in (I/O_0–I/O_7)	Write	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62138EV30LL-45BVXI	51-85149	36-ball Very Fine Pitch BGA (6 mm × 8 mm × 1 mm) (Pb-free)	Industrial

Package Diagrams

36-ball VFBGA (6 x 8 x 1 mm) (51-85149)



Document History Page

Document Title: CY62138EV30 2-Mbit (256K x 8) MoBL® Static RAM Document Number: 38-05577				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	237432	See ECN	AJU	New data sheet
*A	427817	See ECN	NXR	Removed 35 ns Speed Bin Removed “L” version Removed 32-pin TSOPII package from product Offering. Changed ball C3 from DNU to NC. Removed the redundant footnote on DNU. Moved Product Portfolio from Page # 3 to Page #2. Changed I_{CC} (Max) value from 2 mA to 2.5 mA and I_{CC} (Typ) value from 1.5 mA to 2 mA at f = 1 MHz Changed I_{CC} (Typ) value from 12 mA to 15 mA at f = f_{max}=1/t_{RC} Changed I_{SB1} and I_{SB2} Typ. values from 0.7 μA to 1 μA and Max. values from 2.5 μA to 7 μA. Changed V_{CC} stabilization time in footnote #7 from 100 μs to 200 μs Changed the AC test load capacitance from 50pF to 30pF on Page# 4 Changed V_{DR} from 1.5V to 1V on Page# 4. Changed I_{CCDR} from 1 μA to 3 μA in the Data Retention Characteristics table on Page # 4. Corected t_R in Data Retention Characteristics from 100 μs to t_{RC} ns Changed t_{OHA}, t_{LZCE}, t_{LZWE} from 6 ns to 10 ns Changed t_{HZOE}, t_{HZCE}, t_{HZWE} from 15 ns to 18 ns Changed t_{LZOE} from 3 ns to 5 ns Changed t_{SCE} and t_{AW} from 40 ns to 35 ns Changed t_{SD} from 20 ns to 25 ns Changed t_{PWE} from 25 ns to 35 ns Updated the Ordering Information table and replaced Package Name column with Package Diagram.